

FEATURES

- 5.03 mm X 3.89 mm active area
- Low dark current
- Long term stability
- Light detection 628-638 nm

DESCRIPTION

19.57 mm² Low Dark Current Photodiode with P on N construction. Hermetically packaged in an isolated case TO-5 with a clear borosilicate glass window cap and internal 632.8 nm, 10 nm FWHM, 75% transmission bandpass filter. The internal filter is also available with alternate bandwidth and transmission values.

APPLICATIONS

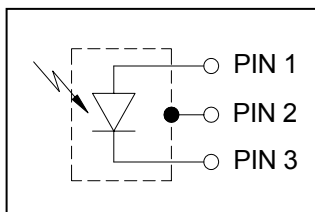
- Precision photometry
- Analytical instruments
- Medical equipment
- Liquid chromatography



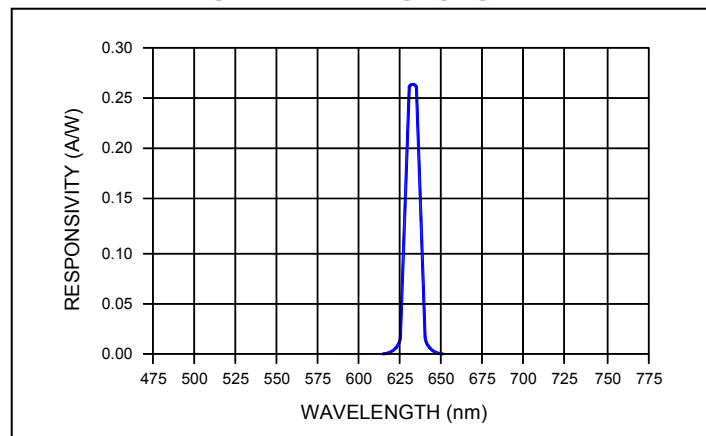
ABSOLUTE MAXIMUM RATING

SYMBOL	PARAMETER	MIN	MAX	UNITS
T _{STG}	Storage Temp	-30	+70	°C
T _{OP}	Operating Temp	-25	+70	°C
V _{R(OP)}	Reverse Operating Voltage	-	50	V
I _{I(PEAK)}	Peak DC Current	-	10	mA

SCHEMATIC



SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS @ 22° C

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
R _{SH}	Shunt Resistance	V _R = ±10 mV	100	200	---	MΩ
I _D	Dark Current	V _R = 5 V	---	0.35	---	nA
C	Capacitance	V _R = 0 V;	---	160	---	pF
		V _R = 5 V;	---	50	---	
	Responsivity	V _R = 0 V; λ = 633 nm	---	0.26	---	A/W
NEP	Noise Equivalent Power	V _R = 5 V; λ = 633 nm; R _L = 50 Ω	---	4.1 X 10 ⁻¹⁴	---	W/Hz ^{1/2}
V _{BR}	Breakdown Voltage	I _R = 10 μA	50	---	---	V
t _r	Rise Time	V _R = 5 V; λ = 633 nm; R _L = 50 Ω	---	30	---	ns

Disclaimer: Due to our policy of continued development, specifications are subject to change without notice.

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